## DISCRETE SEMICONDUCTORS

# DATA SHEET

**PEMH2; PUMH2** NPN/NPN resistor-equipped transistors; R1 = 47 kΩ, R2 = 47 kΩ

Product specification Supersedes data of 2003 Oct 02 2004 Apr 14





UNIT

# NPN/NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

PEMH2; PUMH2

#### **FEATURES**

- Built-in bias resistors
- · Simplifies circuit design
- Reduces component count
- · Reduces pick and place costs.

#### **APPLICATIONS**

- · Low current peripheral driver
- Replacement of general purpose transistors in digital applications
- · Control of IC inputs.

SYMBOL	PARAMETER	TYP.	MAX.	
$V_{CEO}$	collector-emitter	_	50	,
	voltage			

**QUICK REFERENCE DATA** 

	voltage			
Io	output current (DC)	_	100	mA
TR1	NPN	_	_	_
TR2	NPN	_	_	-
R1	bias resistor	47	_	kΩ
R2	bias resistor	47	_	kΩ

#### **DESCRIPTION**

NPN/NPN resistor-equipped transistors (see "Simplified outline, symbol and pinning" for package details).

#### **PRODUCT OVERVIEW**

TYPE NUMBER	PACKA	AGE	MARKING CODE	NPN/PNP	PNP/PNP
TIPE NOMBER	PHILIPS			COMPLEMENT	COMPLEMENT
PEMH2	SOT666	_	Z2	PEMD12	PEMB2
PUMH2	SOT363	SC-88	2*H <sup>(1)</sup>	PUMD12	PUMB2

#### Note

- 1. \* = p: Made in Hong Kong.
  - \* = t: Made in Malaysia.

### SIMPLIFIED OUTLINE, SYMBOL AND PINNING

TYPE NUMBER	SIMPLIFIED OUTLINE AND SYMBOL		PINNING  DESCRIPTION  emitter TR1  base TR1  collector TR2  emitter TR2  base TR2  collector TR1
I TPE NUMBER	SIMPLIFIED OUTLINE AND STMBOL	PIN	
PEMH2	6 5 4	1	emitter TR1
PUMH2		2	base TR1
	$\left  \begin{array}{c c} & & & \\ & & & \\ & & & \\ & & & \\ \end{array} \right $	3	collector TR2
	TR2	4	emitter TR2
		5	base TR2
		6	collector TR1
	1 2 3		
	· WITCU49		

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# NPN/NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

PEMH2; PUMH2

#### **ORDERING INFORMATION**

TYPE NUMBER		PACKAGE	
NAME		DESCRIPTION	VERSION
PEMH2 – plastic surface mounted package; 6 le		plastic surface mounted package; 6 leads	SOT666
PUMH2 – plastic surface mounted package; 6 leads		SOT363	

#### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
Per transist	or			-	
V <sub>CBO</sub>	collector-base voltage	open emitter	_	50	V
V <sub>CEO</sub>	collector-emitter voltage	open base	_	50	V
V <sub>EBO</sub>	emitter-base voltage	open collector	_	10	V
VI	input voltage				
	positive		_	+40	V
	negative		_	-10	V
I <sub>O</sub>	output current (DC)		_	100	mA
I <sub>CM</sub>	peak collector current		_	100	mA
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	200	mW
	SOT666	notes 1 and 2	_	200	mW
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T <sub>amb</sub>	operating ambient temperature		-65	+150	°C
Per device				-	
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> ≤ 25 °C			
	SOT363	note 1	_	300	mW
	SOT666	notes 1 and 2	_	300	mW

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

# NPN/NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

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### THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
Per transist	or			
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	625	K/W
	SOT666	notes 1 and 2	625	K/W
Per device				
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	T <sub>amb</sub> ≤ 25 °C		
	SOT363	note 1	416	K/W
	SOT666	notes 1 and 2	416	K/W

#### **Notes**

- 1. Device mounted on an FR4 printed-circuit board, single-sided copper, standard footprint.
- 2. Reflow soldering is the only recommended soldering method.

#### **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT		
Per transistor								
I <sub>CBO</sub>	collector-base cut-off current	V <sub>CB</sub> = 50 V; I <sub>E</sub> = 0 A	_	_	100	nA		
I <sub>CEO</sub>	collector-emitter cut-off current	V <sub>CE</sub> = 30 V; I <sub>B</sub> = 0 A	_	_	1	μΑ		
		$V_{CE} = 30 \text{ V}; I_{B} = 0 \text{ A}; T_{j} = 150 ^{\circ}\text{C}$	_	_	50	μΑ		
I <sub>EBO</sub>	emitter-base cut-off current	V <sub>EB</sub> = 5 V; I <sub>C</sub> = 0 A	_	_	90	μΑ		
h <sub>FE</sub>	DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}$	80	_	_			
V <sub>CEsat</sub>	collector-emitter saturation voltage	$I_C = 10 \text{ mA}; I_B = 0.5 \text{ mA}$	_	_	150	mV		
$V_{i(off)}$	input off voltage	$V_{CE} = 5 \text{ V}; I_{C} = 100 \mu\text{A}$	_	1.2	0.8	V		
V <sub>i(on)</sub>	input on voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 2 \text{ mA}$	3	1.6	_	V		
R1	input resistor		33	47	61	kΩ		
R2 R1	resistor ratio		0.8	1	1.2			
C <sub>c</sub>	collector capacitance	$V_{CB} = 10 \text{ V}; I_E = I_e = 0 \text{ A};$ f = 1 MHz	_	_	2.5	pF		

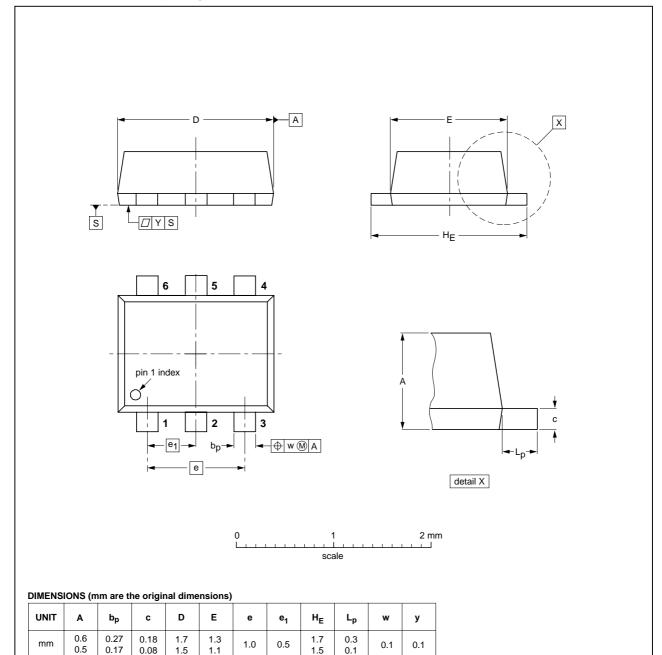
## NPN/NPN resistor-equipped transistors; $R1 = 47 \text{ k}\Omega$ , $R2 = 47 \text{ k}\Omega$

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### **PACKAGE OUTLINES**

### Plastic surface mounted package; 6 leads

**SOT666** 



OUTLINE	REFERENCES EUROPEAN				ISSUE DATE	
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT666						<del>-01-01-04</del> 01-08-27

2004 Apr 14 5

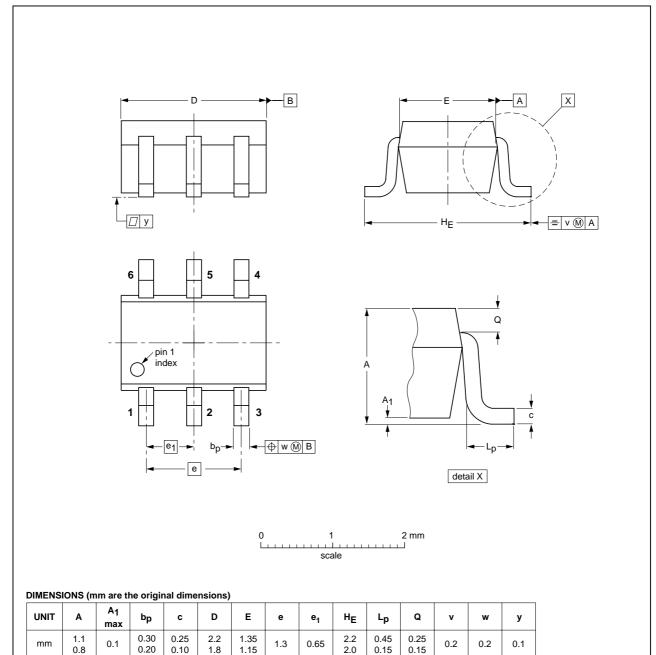
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# NPN/NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

# PEMH2; PUMH2

### Plastic surface mounted package; 6 leads

**SOT363** 



OUTLINE		REFER	ENCES	EUROPEAN ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE	
SOT363			SC-88		97-02-28	

## NPN/NPN resistor-equipped transistors; R1 = 47 k $\Omega$ , R2 = 47 k $\Omega$

PEMH2; PUMH2

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LEVEL	DATA SHEET STATUS <sup>(1)</sup>	PRODUCT STATUS(2)(3)	DEFINITION
I	Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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- 3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

#### **DEFINITIONS**

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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